

## **Power Electronics - Market Share Analysis, Industry Trends & Statistics, Growth Forecasts (2026 - 2031)**

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### **Report description:**

Power Electronics Market Analysis

The power electronics market is expected to grow from USD 26.84 billion in 2025 to USD 28.78 billion in 2026 and is forecast to reach USD 40.81 billion by 2031 at 7.24% CAGR over 2026-2031. Continued migration from legacy silicon systems toward silicon-carbide and gallium-nitride solutions underpins this advance, enabling higher efficiency, power density, and smaller form factors in critical applications. Demand accelerated as automakers scaled electric-vehicle production, utilities upgraded renewable-energy inverters, and data-center operators adopted high-voltage direct-current architectures. Wide-bandgap adoption also benefited from regional policy support that encouraged domestic semiconductor manufacturing and electric-mobility infrastructure. Meanwhile, supply-chain diversification initiatives, especially across Asia-Pacific, bolstered localized production of substrates, epitaxy, and advanced packaging, reducing lead times and transportation risk.

Global Power Electronics Market Trends and Insights

Accelerated adoption of SiC and GaN devices in EV fast-charging infrastructure

European charging-network operators prioritized 800 V architectures that require 1,200 V and 1,700 V SiC MOSFETs to meet grid-connection efficiency targets. Projects backed by incentive programs are standardized on SiC power stages that cut energy losses and shrink cooling subsystems. Collaboration between system integrators and semiconductor suppliers shortened design cycles, while alliance agreements with automotive OEMs ensured long-term volume commitments. Interoperability regulations

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further created a level playing field that favors modular, high-density chargers based on wide-bandgap devices. Successful deployments draw global attention, positioning Europe as the reference market for next-generation fast-charging solutions.

#### Large-scale solar and wind farm inverter upgrades in Asia

Utility-scale solar farms in China, India, and Vietnam replaced legacy silicon inverters with SiC-based modules that withstand high switching frequencies in hot, humid environments. Wolfspeed's latest utility modules provided the thermal-cycling reliability demanded by centralized 3 MW to 5 MW inverters. Offshore wind developers adopted similar power stages to meet size and weight limits on turbine nacelles. Regional contract manufacturers localized assembly to avoid import duties, accelerating price parity with conventional silicon alternatives. These upgrades align with government renewable portfolio standards, keeping energy tariffs competitive across emerging economies.

#### Supply-chain bottlenecks for 150 mm and larger SiC wafers

Chronic substrate shortages constrained volume ramps, keeping average selling prices elevated. Wolfspeed's temporary liquidity challenges increased risk exposure for partners that relied on its 200 mm roadmap, leading Renesas to exit its planned SiC platform. Chinese entrants accelerated capacity additions yet faced qualification hurdles with automotive customers. The multiyear lag between announced fabs and production readiness complicated demand-forecast accuracy for both device makers and system OEMs. As a result, several automakers executed dual-sourcing strategies to hedge wafer allocations.

Other drivers and restraints analyzed in the detailed report include:

5G base-station roll-outs requiring high-efficiency RF power amplifiers  
Electrification of industrial motor drives above 7.5 kW in Southeast Asia  
Packaging thermal-management constraints above 1.2 kV modules

For complete list of drivers and restraints, kindly check the Table Of Contents.

#### Segment Analysis

Power modules delivered 8.49% CAGR through 2031 as design teams opted for pre-packaged assemblies that simplify thermal layout and electromagnetic shielding. In 2025, discrete transistors and diodes still contributed 45.92% of revenue, preserving flexibility in consumer and low-power factory equipment. Demand for modules surged in traction inverters and renewable-energy converters above 50 kW where integrating gate drivers, temperature sensors, and isolation reduced development cycles. Embedded-cooling substrates entered pilot production, pushing module power density upward and enabling smaller inverter housings in electric vehicles. Integrated power ICs gained share in fast-charger adapters below 100 W, combining control and switching in a single plastic package that meets stringent size constraints. Smartphone brands adopted these monolithic GaN solutions to achieve 65 W charging in compact wall plugs. The power electronics market size for modules is forecast to expand steadily as automotive suppliers transition to 800 V platforms, while consumer design wins sustain volume in discrete devices.

Market-wide standardization on transfer-molded packages offered cost reductions and better moisture resistance for industrial drives operating in harsh climates. Manufacturers leveraged automated assembly lines to meet rising output needs, particularly across Asia-Pacific. Discrete devices nevertheless preserved a sizeable presence in lighting ballasts, home appliances, and robotic controllers, where customized board layouts and diverse voltage classes outweighed the integration advantage. Over the forecast span, increased silicon-carbide wafer availability will further tilt the share toward modules, yet discrete volumes will decline gradually rather than collapse.

MOSFETs captured 43.62% of 2025 revenue and their 8.98% CAGR positions them as both the largest and fastest-growing device

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category. The architecture lends itself to incremental R&D, evident in Wolfspeed's Gen 4 platform that reduced on-state resistance while maintaining familiar gate-drive requirements. High-frequency resonance topologies in charger adapters and solar micro-inverters gravitated to GaN enhancement-mode MOSFETs, whereas SiC planar MOSFETs excelled in vehicle traction stages above 100 kW. IGBTs remained essential in rail propulsion and large industrial drives, sustaining demand in power classes beyond practical MOSFET limits. Thyristors continued serving grid-tied soft-starters and HVDC links, though their overall contribution shrank.

Device-makers introduced co-packaged Schottky diodes with SiC MOSFETs, easing reverse-recovery constraints and simplifying board layouts. Meanwhile, gallium-nitride suppliers improved dynamic-RDS(on) behavior to extend device life in hard-switching conditions. The power electronics market continues to reward MOSFET innovation because the form factor aligns with existing driver ecosystems, lowering design barriers for system engineers. Future share shifts will hinge on wide-bandgap wafer pricing and the speed of automotive qualification for next-generation MOSFET gates.

Power Electronics Market is Segmented by Component (Discrete, Module, and Integrated Power IC), Device Type (MOSFET, IGBT, Thyristor, and Diode), Material (Silicon, Silicon Carbide, and More), End-User Industry (Consumer Electronics, Automotive, ICT and Telecommunication, Industrial, Energy and Power, Aerospace and Defense, and More), and Geography (North America, Europe, Asia-Pacific, South America, Middle East and Africa).

### Geography Analysis

Asia-Pacific generated 53.88% of global revenue in 2025 and is widening its lead with a 10.05% CAGR. National programs in China, Japan, and South Korea funded wafer fabs, module assembly, and electric-vehicle supply chains, ensuring local availability of substrates and advanced packaging. Japanese authorities pledged USD 67 billion to support domestic semiconductor fleets, aiding companies such as Sony and Mitsubishi Electric, and reinforcing university research collaborations. Mainland China leveraged economies of scale in material growth and backend assembly to supply regional customers quickly, lowering landed cost despite technology gaps in the leading edge.

North America remained the second-largest region, pairing innovation strengths with thriving end-markets in AI servers, electric pickup trucks, and renewable microgrids. State-level incentives attracted new SiC wafer plants and helped secure capital for 200 mm transitions. Defense procurement continued to fund radiation-tolerant GaN research, which later filtered into commercial telecom systems. The power electronics market size in North America is on an upward trajectory as data-center operators adopt 400 V DC architectures that reduce copper usage and improve rack density. Europe focused resources on e-mobility charging corridors and grid-level storage. Policymakers mandated interoperability of charging hardware, indirectly favoring SiC adoption due to its efficiency at 800 V. Automotive Tier 1 suppliers partnered with semiconductor vendors to co-develop traction inverters, creating integrated reference platforms that accelerate homologation. The Middle East and Africa region, while starting from a smaller base, invested in large photovoltaic plants and desalination facilities that require robust inverter stages. South America's opportunities emerged from wind corridors in Brazil and Argentina and from local content rules that encourage assembly of power modules within the region. Collectively, these dynamics keep the power electronics market expanding on every continent, though rates vary with industrial maturity and policy support.

### List of Companies Covered in this Report:

Infineon Technologies AG Mitsubishi Electric Corporation ON Semiconductor Corporation STMicroelectronics N.V. Texas Instruments Inc. ROHM Co., Ltd. ABB Ltd. Toshiba Electronic Devices & Storage Corp. Vishay Intertechnology Inc. Renesas Electronics Corp. Wolfspeed Inc. Fuji Electric Co., Ltd. SEMIKRON Danfoss Littelfuse Inc. GeneSiC Semiconductor Navitas Semiconductor Corp. GaN Systems Inc. Alpha & Omega Semiconductor Microchip Technology Inc. Diodes Incorporated

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Additional Benefits:

<ul> The market estimate (ME) sheet in Excel format  
3 months of analyst support </ul>

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6.4.14 Littelfuse Inc.

6.4.15 GeneSiC Semiconductor

6.4.16 Navitas Semiconductor Corp.

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